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(71) **Applicant**: **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(72) **Inventors; and**
(71) **Applicants** : **LUBOMIRSKY, Dmitry** [US/US]; 862 Bette Avenue, Cupertino, California 95014 (US). **NEMANI, Srinivas** [US/US]; 504 Fern Ridge Court, Sunnyvale, California 94087 (US). **YIEH, Ellie** [US/US]; 5888 Pistoia Way, San Jose, California 95138 (US). **BELOSTOTSKIY, Sergey G.** [RU/US]; 592 Lynxwood Court, Sunnyvale, California 94086 (US).

(74) **Agents**: **BERNADICOU, Michael A.** et al.; Blakely, Sokoloff, Taylor & Zafman LLP, 1279 Oakmead Parkway, Sunnyvale, California 94085 (US).

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(54) **Title**: PROCESS CHAMBER FOR ETCHING LOW K AND OTHER DIELECTRIC FILMS

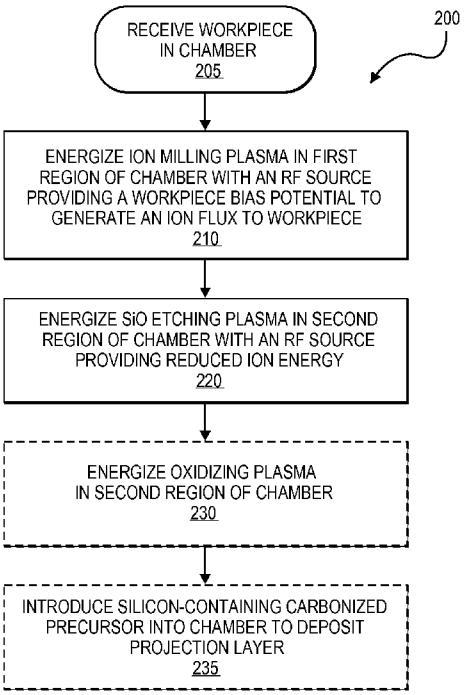


FIG. 2

(57) **Abstract**: Methods and process chambers for etching of low-k and other dielectric films are described. For example, a method includes modifying portions of the low-k dielectric layer with a plasma process. The modified portions of the low-k dielectric layer are etched selectively over a mask layer and unmodified portions of the low-k dielectric layer. Etch chambers having multiple chamber regions for alternately generating distinct plasmas are described. In embodiments, a first charge coupled plasma source is provided to generate an ion flux to a workpiece in one operational mode, while a secondary plasma source is provided to provide reactive species flux without significant ion flux to the workpiece in another operational mode. A controller operates to cycle the operational modes repeatedly over time to remove a desired cumulative amount of the dielectric material.

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